

## VN02HSP

### HIGH SIDE SMART POWER SOLID STATE RELAY

TYPE	VDSS	R <sub>DS(on</sub> )	lout	Vcc
VN02HSP	60 V	0.4 Ω	6 A	36 V

- OUTPUT CURRENT (CONTINUOUS): 6A @ T<sub>c</sub>=25°C
- 5V LOGIC LEVEL COMPATIBLE INPUT
- THERMAL SHUT-DOWN
- UNDER VOLTAGE SHUT-DOWN
- OPEN DRAIN DIAGNOSTIC OUTPUT
- VERY LOW STAND-BY POWER DISSIPATION

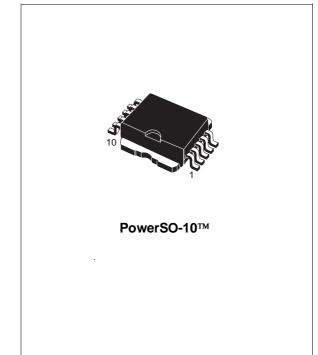
#### DESCRIPTION

The VN02HSP is a monolithic devices made using STMicroelectronics VIPower Technology, intended for driving resistive or inductive loads with one side grounded.

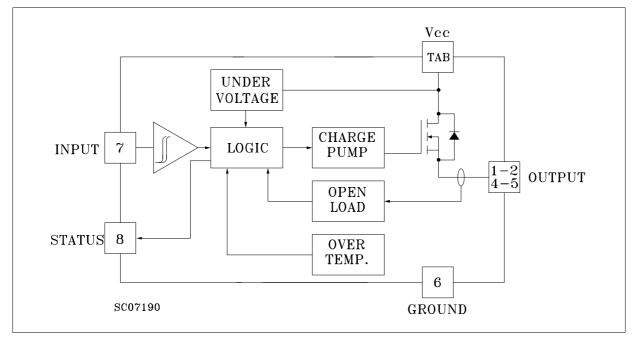
Built-in thermal shut-down protects the chip from over temperature and short circuit.

The input control is 5V logic level compatible.

The open drain diagnostic output indicates open circuit (no load) and over temperature status.



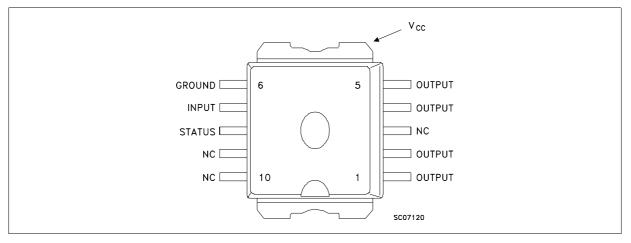
#### **BLOCK DIAGRAM**



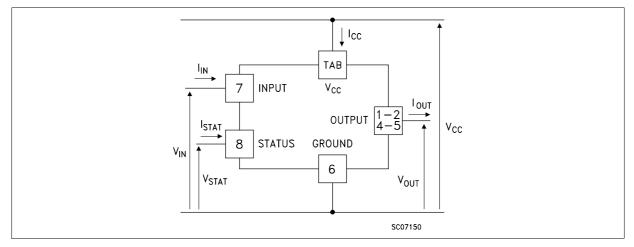
#### ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	60	V
I <sub>OUT</sub>	Output Current (cont.)	6	A
I <sub>R</sub>	Reverse Output Current	-6	A
l <sub>in</sub>	Input Current	±10	mA
-Vcc	Reverse Supply Voltage	-4	V
ISTAT	Status Current	±10	mA
$V_{\text{ESD}}$	Electrostatic Discharge (1.5 kΩ, 100 pF)	2000	V
Ptot	Power Dissipation at $T_c \le 25$ °C	29	W
Tj	Junction Operating Temperature	-40 to 150	°C
T <sub>stg</sub>	Storage Temperature	-55 to 150	°C

#### CONNECTION DIAGRAMS



#### CURRENT AND VOLTAGE CONVENTIONS



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#### THERMAL DATA

R <sub>thj-case</sub>	Thermal Desistance, hunstice explicat	Max	4.35	°C/W
R <sub>thj-amb</sub>		Max	50	°C/W

# **ELECTRICAL CHARACTERISTICS** (V<sub>CC</sub> = 9 to 36 V; -40 $\leq$ T<sub>j</sub> $\leq$ 125 $^oC$ unless otherwise specified) POWER

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>CC</sub>	Supply Voltage	see note 1	5		36	V
Ron	On State Resistance	$I_{OUT} = 3 A$ $I_{OUT} = 3 A$ $T_j = 25 \ ^{\circ}C$			0.8 0.4	Ω Ω
Is	Supply Current	$\begin{array}{lll} \mbox{Off State} & T_j \geq 25 \ ^o\mbox{C} \\ \mbox{On State} & \end{array}$			50 20	μA mA

#### SWITCHING

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
t <sub>d(on)</sub>	Turn-on Delay Time Of Output Current	$I_{OUT}$ = 3 A Resistive Load Input Rise Time < 0.1 µs T <sub>j</sub> = 25 °C	5	10	20	μs
tr	Rise Time Of Output Current	$I_{OUT}$ = 3 A Resistive Load Input Rise Time < 0.1 $\mu$ s T <sub>j</sub> = 25 °C	5	15	45	μs
t <sub>d(off)</sub>	Turn-off Delay Time Of Output Current	$I_{OUT}$ = 3 A Resistive Load Input Rise Time < 0.1 $\mu$ s T <sub>j</sub> = 25 °C	5	15	30	μs
t <sub>f</sub>	Fall Time Of Output Current	$I_{OUT}$ = 3 A Resistive Load Input Rise Time < 0.1 $\mu$ s T <sub>j</sub> = 25 °C	2	6	15	μs
(di/dt) <sub>on</sub>	Turn-on Current Slope	$    I_{OUT} = 3 A     I_{OUT} = I_{OV} $	0.05	0.15	0.5 2	A/μs A/μs
(di/dt) <sub>off</sub>	Turn-off Current Slope	$I_{OUT} = 3 \text{ A}$ $I_{OUT} = I_{OV}$ $25 \le T_j \le 140 ^{\circ}\text{C}$	0.1	0.4	2 4	A/μs A/μs
$V_{demag}$	Inductive Load Clamp Voltage	I <sub>OUT</sub> = 3 A L = 1 mH	-7	-4	-2	V

#### LOGIC INPUT

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
VIL	Input Low Level Voltage				0.8	V
Vih	Input High Level Voltage		2		(*)	V
VI(hyst.)	Input Hysteresis Voltage			0.5		V
l <sub>IN</sub>	Input Current	$V_{IN} = 5 V$		250	500	μA
VICL	Input Clamp Voltage	I <sub>IN</sub> = 10 mA I <sub>IN</sub> = -10 mA	5.5	6 -0.7	-0.3	V V

#### ELECTRICAL CHARACTERISTICS (continued)

PROTECTION AND DIAGNOSTICS

Symbol	Parameter	Test Co	nditions	Min.	Тур.	Max.	Unit
$V_{STAT}$ (•)	Status Voltage Output Low	I <sub>STAT</sub> = 1.6 mA				0.4	V
Vusd	Under Voltage Shut Down			2.5		5	V
V <sub>SCL</sub> (•)	Status Clamp Voltage	I <sub>STAT</sub> = 10 mA I <sub>STAT</sub> = -10 mA		5.5	6 -0.7	-0.3	V V
t <sub>SC</sub>	Switch-off Time in Short Circuit Condition at Start-Up	$R_{LOAD} < 10 m\Omega$ $T_c = 25 °C$	V <sub>CC</sub> = 13 V		1.5	5	ms
lov	Over Current	$R_{LOAD}$ < 10 m $\Omega$	$V_{CC} = 13 V$			28	А
I <sub>AV</sub>	Average Current in Short Circuit	$R_{LOAD} < 10 m\Omega$ $T_c = 85 °C$	V <sub>CC</sub> = 13 V		0.9	1.8	A
I <sub>OL</sub>	Open Load Current Level	9 < V <sub>CC</sub> < 32 V		5		70	mA
Іоит	Leakage Current	Off State	$V_{OUT} = 0 V$			60	μA
T <sub>TSD</sub>	Thermal Shut-down Temperature			140	160		°C
T <sub>R</sub>	Reset Temperature			125	145		°C

(\*) The V<sub>IH</sub> is internally clamped at 6V about. It is possible to connect this pin to an higher voltage via an external resistor calculated to not exceed 10 mA at the input pin.

(•) Status determination > 100 ms after the switching edge.

Note 1 : Above  $V_{CC}$  = 36 V the output voltage is clamped to 36 V. Power dissipation increases and the device turns off if junction temperature reaches thermal shutdown temperature.

#### FUNCTIONAL DESCRIPTION

The device has a diagnostic output which indicates open circuit (no load) and over temperature conditions. The output signals are processed by internal logic.

To protect the device against short circuit and over-current condition the thermal protection turns the integrated Power MOS off at a minimum junction temperature of 140 °C. When the temperature returns to about 125 °C the switch is automatically turned on again. To ensur the protection in all V<sub>CC</sub> conditions and in all the junction temperature range it is necessary to limit the voltage drop across Drain and Source (pin 3 and 5) at 29 V. The device is able to withstand a load dump according the test pulse 5 at level III of the ISO TR/1 7631.

Above  $V_{CC} = 36V$  the output voltage is clamped to 36V. Power dissipation increases and the device turns off if junction temperature reaches thermal shutdown temperature.

# PROTECTING THE DEVICE AGAINST REVERSE BATTERY

The simplest way to protect the device against a continuous reverse battery voltage (-26V) is to

insert a Schottky diode between pin 1 (GND) and ground, as shown in the typical application circuit (fig. 3).

The consequences of the voltage drop across this diode are as follows:

- If the input is pulled to power GND, a negative voltage of -V<sub>F</sub> is seen by the device. (V<sub>IL</sub>, V<sub>IH</sub> thresholds and V<sub>STAT</sub> are increased by V<sub>F</sub> with respect to power GND).
- The undervoltage shutdown level is increased by  $\mathsf{V}_\mathsf{F}.$

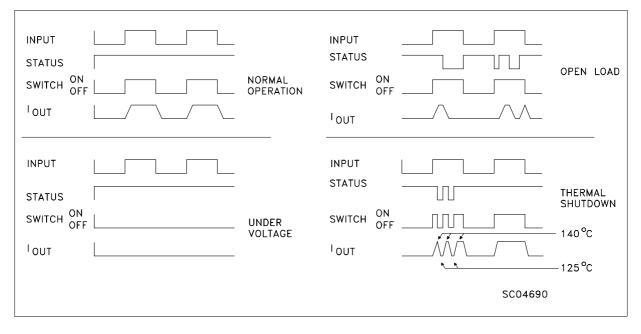
If there is no need for the control unit to handle external analog signals referred to the power GND, the best approach is to connect the reference potential of the control unit to node [1] (see application circuit infig. 4), which becomes the common signal GND for the whole control board.

In this way no shift of  $V_{IH}$ ,  $V_{IL}$  and  $V_{STAT}$  takes place and no negative voltage appears on the INPUT pin; this solution allows the use of a standard diode, with a breakdown voltage able to handle any ISO normalized negative pulses that occours in the automotive environment.

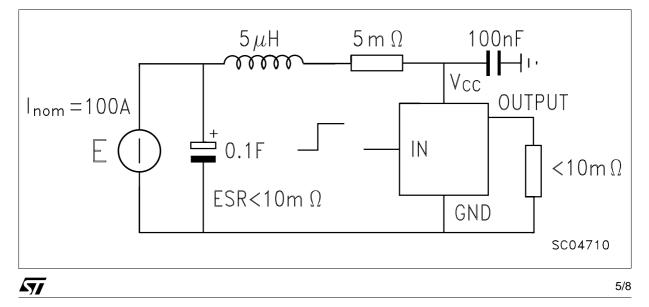
#### **TRUTH TABLE**

	INPUT	OUTPUT	DIAGNOSTIC
Normal Operation	L	L	Н
	Н	Н	Н
Open Circuit (No Load)	L	L	Н
	Н	Н	L
Over-temperature	L	L	Н
	Н	Н	L
Under-voltage	L	L	Н
	Н	L	Н

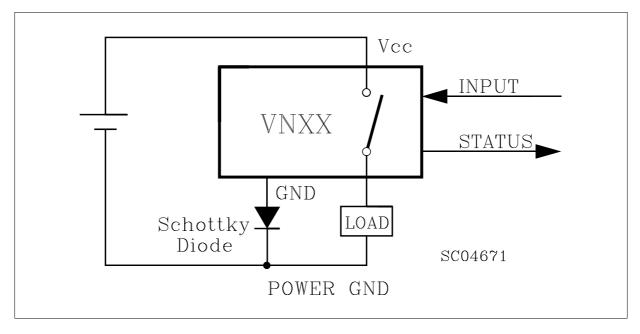
#### Figure 1: Waveforms

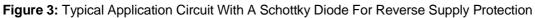


#### Figure 2: Over Current Test Circuit

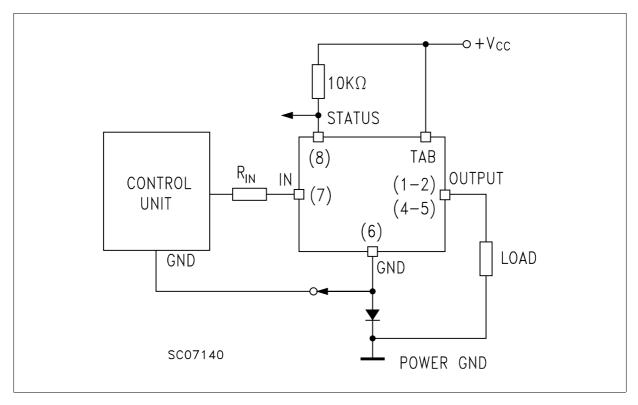


#### VN02HSP





#### Figure 4: Typical Application Circuit With Separate Signal Ground

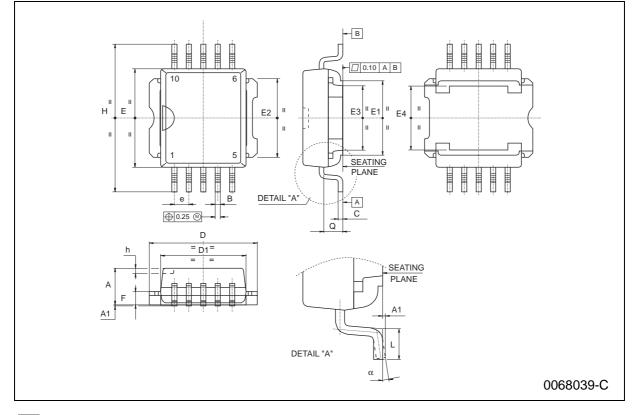


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DIM.		mm			inch	
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	3.35		3.65	0.132		0.144
A1	0.00		0.10	0.000		0.004
В	0.40		0.60	0.016		0.024
С	0.35		0.55	0.013		0.022
D	9.40		9.60	0.370		0.378
D1	7.40		7.60	0.291		0.300
Е	9.30		9.50	0.366		0.374
E1	7.20		7.40	0.283		0.291
E2	7.20		7.60	0.283		0.300
E3	6.10		6.35	0.240		0.250
E4	5.90		6.10	0.232		0.240
е		1.27			0.050	
F	1.25		1.35	0.049		0.053
Н	13.80		14.40	0.543		0.567
h		0.50			0.002	
L	1.20		1.80	0.047		0.071
q		1.70			0.067	
α	0 <sup>°</sup>		8°			





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